

SAMSUNG SEMICONDUCTOR INC.

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KSA1298

PNP EPITAXIAL SILICON TRANSISTOR

T-29-15

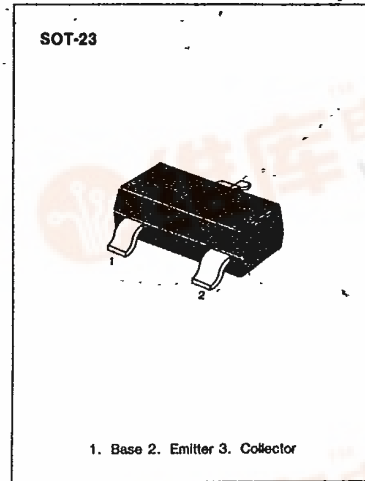
LOW FREQUENCY AMPLIFIER

• Complement to KSC3285

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-30	V
Collector-Emitter Voltage	V _{CE0}	-25	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _c	-800	mA
Base Current	I _b	-160	mA
Collector Dissipation	P _c	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55~150	°C

• Refer to KSA643 for graphs.



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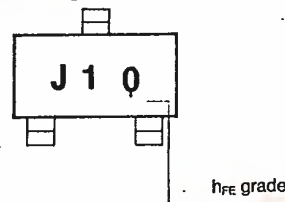
ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = -10mA, I _b = 0	-25			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -1mA, I _C = 0	-5			V
Collector Cutoff Current	I _{CB0}	V _{CB} = -30V, I _E = 0			-100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} = -5V, I _C = 0			-100	nA
DC Current Gain	h _{FE1}	V _{CE} = -1V, I _C = -100mA	100		320	
	h _{FE2}	V _{CE} = -1V, I _C = -800mA	40			
Collector Emitter Saturation Voltage	V _{CE (sat)}	I _C = -500mA, I _b = -20mA			-0.4	V
Base-Emitter (on) Voltage	V _{BE (on)}	V _{CE} = -1V, I _C = -10mA	-0.5		-0.8	V
Current Gain-Bandwidth Product	f _T	V _{CE} = -5V, I _C = -10mA		120		MHz
Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0 f = 1MHz		13		pF

h_{FE} (1) CLASSIFICATION

Classification	O	Y
h _{FE} (1)	100-200	160-320

Marking



SAMSUNG SEMICONDUCTOR

